

|   | Type | L # | Hits        | Search Text  | DBs  | Time Stamp          |
|---|------|-----|-------------|--|--|---------------------|
| 1 | BRS  | L1  | 15748       | (plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:03 |
| 2 | BRS  | L2  | 21430       | tetraethylorthosilicate or TEOS                                      | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:03 |
| 3 | BRS  | L4  | 141731<br>7 | trench or gap or plug  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:04 |
| 4 | BRS  | L5  | 132762<br>6 | oxide or SiO   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:05 |
| 5 | BRS  | L6  | 388012<br>4 | remov\$6 or etch\$6  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:06 |

|    | Type | L # | Hits  | Search Text  | DBs  | Time Stamp          |
|----|------|-----|-------|--|--|---------------------|
| 6  | BRS  | L7  | 73374 | MOSFET or "metal oxide semiconductor field effect" | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:06 |
| 7  | BRS  | L9  | 9931  | 6 near8 5 near8 4                                  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:09 |
| 8  | BRS  | L10 | 1060  | 9 and 1  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:11 |
| 9  | BRS  | L11 | 548   | 10 and 2   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:11 |
| 10 | BRS  | L12 | 108   | 11 and 7   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:49 |

|    | Type | L # | Hits  | Search Text  | DBs  | Time Stamp          |
|----|------|-----|-------|--|--|---------------------|
| 11 | BRS  | L13 | 35535 | wetch-etching or<br>wetch-etched or wet-etch or<br>(wet adj etch\$6) | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:50 |
| 12 | BRS  | L14 | 2975  | 9 and 13   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:51 |
| 13 | BRS  | L15 | 988   | 9 same 13  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:51 |
| 14 | BRS  | L16 | 197   | 15 and 7   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:51 |
| 15 | IS&R | L43 | 1671  | (438/270).CCLS.  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>18:21 |

|   | Type | L # | Hits        | Search Text  | DBs  | Time Stamp          |
|---|------|-----|-------------|--|--|---------------------|
| 1 | BRS  | L1  | 15748       | (plasma adj enhanced adj<br>chemical adj vapor adj<br>deposition) or PECVD | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:03 |
| 2 | BRS  | L2  | 21430       | tetraethylorthosilicate or<br>TEOS   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:03 |
| 3 | BRS  | L4  | 141731<br>7 | trench or gap or plug  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:04 |
| 4 | BRS  | L5  | 132762<br>6 | oxide or SiO   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:05 |
| 5 | BRS  | L6  | 388012<br>4 | remov\$6 or etch\$6  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:06 |

|    | Type | L # | Hits  | Search Text  | DBs  | Time Stamp          |
|----|------|-----|-------|--|--|---------------------|
| 6  | BRS  | L7  | 73374 | MOSFET or "metal oxide semiconductor field effect" | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:06 |
| 7  | BRS  | L9  | 9931  | 6 near8 5 near8 4                                  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:09 |
| 8  | BRS  | L10 | 1060  | 9 and 1  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:11 |
| 9  | BRS  | L11 | 548   | 10 and 2   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:11 |
| 10 | BRS  | L12 | 108   | 11 and 7   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:49 |

|    | Type | L # | Hits  | Search Text  | DBs  | Time Stamp          |
|----|------|-----|-------|--|--|---------------------|
| 11 | BRS  | L13 | 35535 | wetch-etching or<br>wetch-etched or wet-etch or<br>(wet adj etch\$6) | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:50 |
| 12 | BRS  | L14 | 2975  | 9 and 13   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:51 |
| 13 | BRS  | L15 | 988   | 9 same 13  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:51 |
| 14 | BRS  | L16 | 197   | 15 and 7   | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>16:51 |
| 15 | IS&R | L43 | 1671  | (438/270).CCLS.  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>18:21 |

|    | Type | L # | Hits | Search Text     | DBs  | Time Stamp          |
|----|------|-----|------|-----------------|--|---------------------|
| 16 | IS&R | L44 | 89   | (438/269).CCLS. | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>18:22 |
| 17 | IS&R | L45 | 1208 | (438/424).CCLS. | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>18:22 |
| 18 | IS&R | L46 | 687  | (438/633).CCLS. | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>18:22 |
| 19 | IS&R | L47 | 956  | (438/689).CCLS. | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>18:22 |
| 20 | IS&R | L48 | 605  | (438/691).CCLS. | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>18:22 |

|    | Type | L # | Hits | Search Text      | DBs  | Time Stamp          |
|----|------|-----|------|------------------|--|---------------------|
| 21 | IS&R | L49 | 1807 | (438/692) .CCLS. | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/05<br>18:22 |



|   | Type | L # | Hits  | Search Text  | DBs  | Time Stamp          |
|---|------|-----|-------|--|--|---------------------|
| 1 | IS&R | L1  | 965   | (438/689).CCLS.  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/06<br>14:04 |
| 2 | IS&R | L2  | 689   | (438/633).CCLS.  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/06<br>14:26 |
| 3 | BRS  | L3  | 35616 | wetch-etching or<br>wetch-etched or wet-etch or<br>(wet adj etch\$6) | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/06<br>14:27 |
| 4 | BRS  | L4  | 158   | 3 near4 oxide near4<br>trench\$6                                     | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/06<br>14:27 |
| 5 | IS&R | L5  | 605   | (438/691).CCLS.  | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/06<br>14:45 |

|   | Type | L # | Hits | Search Text     | DBs  | Time Stamp          |
|---|------|-----|------|-----------------|--|---------------------|
| 6 | IS&R | L6  | 1809 | (438/692).CCLS. | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/06<br>15:36 |
| 7 | IS&R | L7  | 1672 | (438/270).CCLS. | USPAT;<br>US-PGP<br>UB;<br>EPO;<br>JPO;<br>DERWEN<br>T;<br>IBM_TD<br>B | 2004/05/06<br>15:42 |

|    | Type | Hits    | Search Text  |
|----|------|---------|--|
| 1  | BRS  | 15748   | (plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD   |
| 2  | BRS  | 21430   | tetraethylorthosilicate or TEOS  |
| 3  | BRS  | 1417317 | trench or gap or plug  |
| 4  | BRS  | 1327626 | oxide or SiO   |
| 5  | BRS  | 3880124 | remov\$6 or etch\$6  |
| 6  | BRS  | 73374   | MOSFET or "metal oxide semiconductor field effect"   |
| 7  | BRS  | 9931    | (remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)   |
| 8  | BRS  | 1060    | ((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)  |
| 9  | BRS  | 548     | ((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)) and (tetraethylorthosilicate or TEOS)   |
| 10 | BRS  | 108     | ((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and ((plasma adj enhanced adj chemical adj vapor adj deposition) or PECVD)) and (tetraethylorthosilicate or TEOS)) and (MOSFET or "metal oxide semiconductor field effect") |
| 11 | BRS  | 2975    | ((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) and (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6) )   |
| 12 | BRS  | 988     | ((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) same (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6) )  |

|    | DBs   | Time Stamp       |
|----|---|------------------|
| 1  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:03 |
| 2  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:03 |
| 3  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:04 |
| 4  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:05 |
| 5  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:06 |
| 6  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:06 |
| 7  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:09 |
| 8  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:11 |
| 9  | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:11 |
| 10 | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:49 |
| 11 | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:51 |
| 12 | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:51 |

|    | Type | Hits | Search Text   |
|----|------|------|---|
| 13 | BRS  | 197  | ((remov\$6 or etch\$6) near8 (oxide or SiO) near8 (trench or gap or plug)) same (wetch-etching or wetch-etched or wet-etch or (wet adj etch\$6) )) and (MOSFET or "metal oxide semiconductor field effect") |
| 14 | IS&R | 2    | ("20020081817").PN.   |
| 15 | IS&R | 89   | (438/269).CCLS.   |
| 16 | IS&R | 1212 | (438/424).CCLS.   |

|    | DBs   | Time Stamp       |
|----|---|------------------|
| 13 | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/05 16:51 |
| 14 | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/06 09:48 |
| 15 | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/06 10:14 |
| 16 | USPAT; US-PGPUB;<br>EPO; JPO; DERWENT;<br>IBM_TDB | 2004/05/06 10:37 |